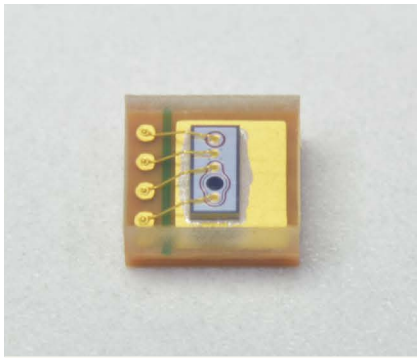


Si APD

S15413-02



High-speed, compact Si APD that does not require temperature adjustment

The S15413-02 is a gain-stabilized APD (GS APD) with a built-in temperature compensation function inside the sensor. This realizes constant gain without the need for temperature adjustment. It is suitable for laser monitors of optical rangefinders used in a wide range of applications, from consumer to industrial.

Features

- Built-in temperature compensation function
- Compact package: 2.0 × 1.8 × 0.85[†] mm
- Peak sensitivity wavelength: 760 nm (M=50)
- High-speed response: Cutoff frequency=1.5 GHz typ. (λ=660 nm, M=50)

Applications

- Optical rangefinders

Structure

Parameter	Specification	Unit
Photosensitive area*1	φ0.2	mm
Package	Glass epoxy	-
Sealing material	Silicone resin	-

*1: Area in which a typical gain can be obtained

Absolute maximum ratings

Parameter	Symbol	Specification	Unit
Anode reverse current (DC)	I _r anode max	0.1	mA
Forward current	I _F max	10	mA
Operating temperature*2	T _{opr}	-30 to +105	°C
Storage temperature*2	T _{stg}	-40 to +105	°C
Soldering temperature	T _{sol}	260 (3 times)*3	°C

*2: No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environments, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

*3: Reflow soldering, JEDEC J-STD-020 MSL 2a, see P.5

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

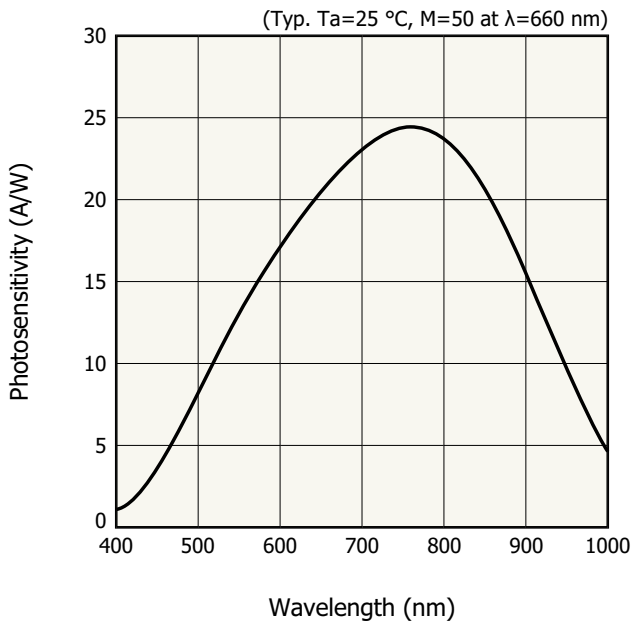
Electrical and optical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Spectral response range	λ			400 to 1000		nm
Peak sensitivity wavelength	λ_p		-	760	-	nm
Photosensitivity	S	$\lambda=660$ nm, M=1	-	0.42	-	A/W
Quantum efficiency	QE	$\lambda=660$ nm, M=1	-	85	-	%
Operating reverse voltage	Vop	Gain-stabilized mode operation*4	$110 + 0.42 \times (T_{a\text{ opr}} - 25)^{*5}$	-	-	V
Temperature coefficient of operating reverse voltage	ΔT_{Vop}		-	0.42	-	V/°C
Dark current	ID	Gain-stabilized mode operation*4	-	10	100	pA
Dark current temperature coefficient	ΔT_{ID}	M=50	-	1.1	-	times/°C
Cutoff frequency	fc	M=50, RL=50 Ω $\lambda=660$ nm, -3 dB	-	1.5	-	GHz
Terminal capacitance	Ct	M=50, f=1 MHz	-	0.6	-	pF
Excess noise figure	x	M=50, $\lambda=660$ nm	-	0.3	-	-
Gain	M	Gain-stabilized mode operation*4, $\lambda=660$ nm	40	50	60	-
Gain control range	-	$\lambda=660$ nm	-	30 to 100	-	-

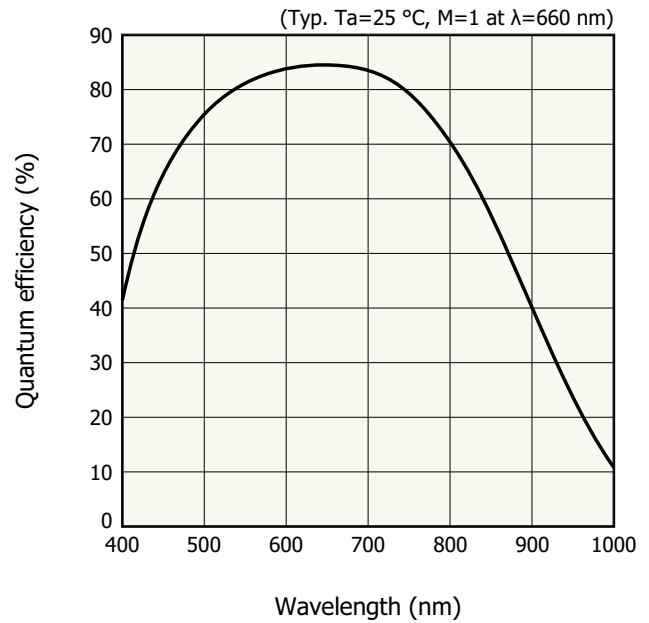
*4: Apply bias voltage to anode. IR anode limit=10 μ A, guard pin=GND

*5: Ta opr=assumed maximum operating temperature

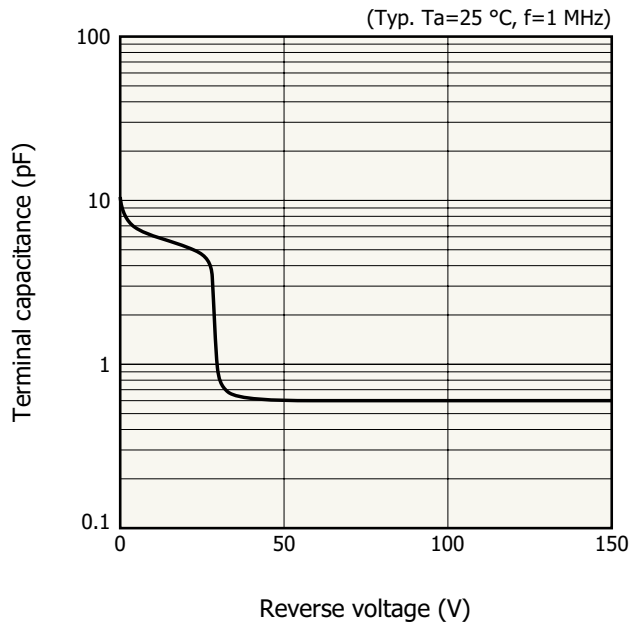
Spectral response



Quantum efficiency vs. wavelength

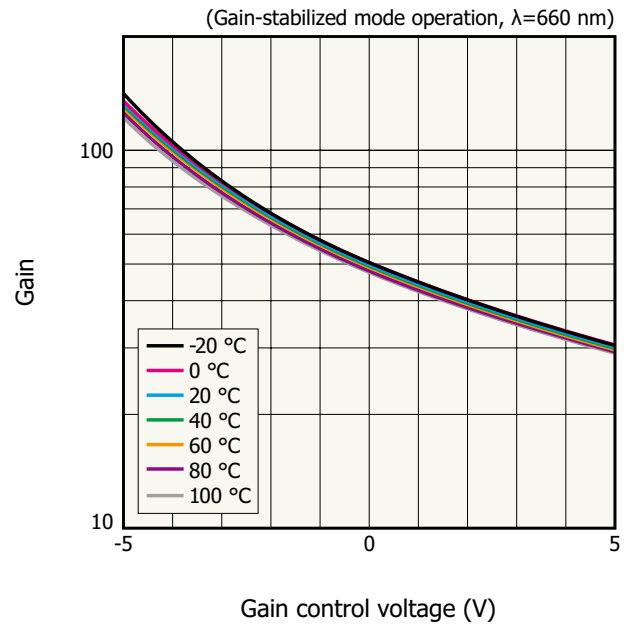


Terminal capacitance vs. reverse voltage



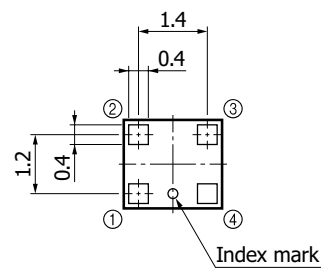
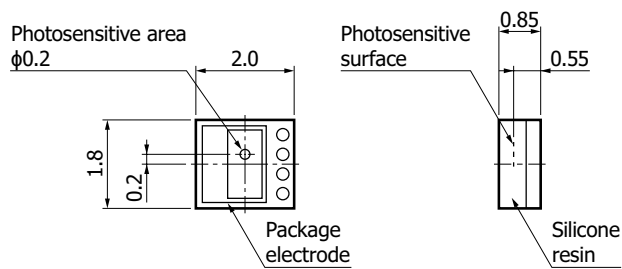
KAPDB0655EA

Gain vs. gain control voltage (typical example)

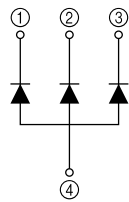


KAPDB0656EA

Dimensional outlines (unit: mm)



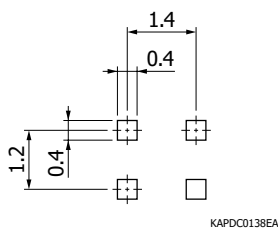
Tolerance unless otherwise noted: ± 0.2
 Chip position accuracy with respect to package electrode pattern center: X, Y $\leq \pm 0.2$



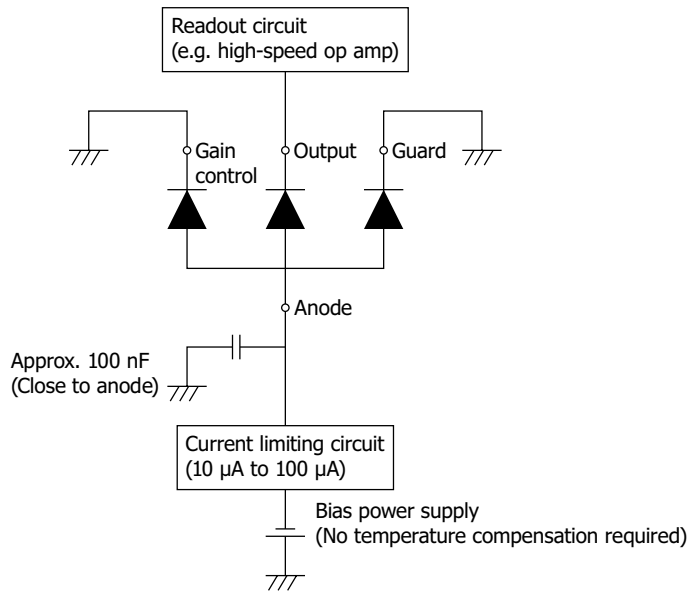
①	Gain control	Gain control voltage input (connect to GND)
②	Output	APD output
③	Guard	Leakage current output (connect to GND)
④	Anode	Bias voltage input

KAPDA0229EA

Recommended land pattern



Connection example



- The gain can be controlled by applying a voltage to the gain pin.
- We recommend connecting a capacitor near the anode pin to stabilize the bias voltage.

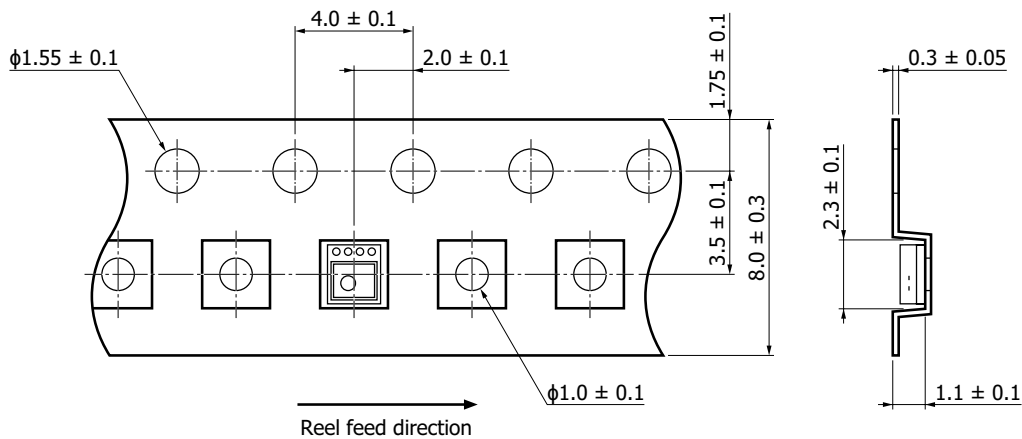
KAPDC0137EA

Standard packing specifications

- Reel (conforms to JEITA ET-7200)

Appearance	Hub diameter	Tape width	Material	Electrostatic characteristics
$\phi 180$ mm	$\phi 60$ mm	8 mm	PS	Conductive

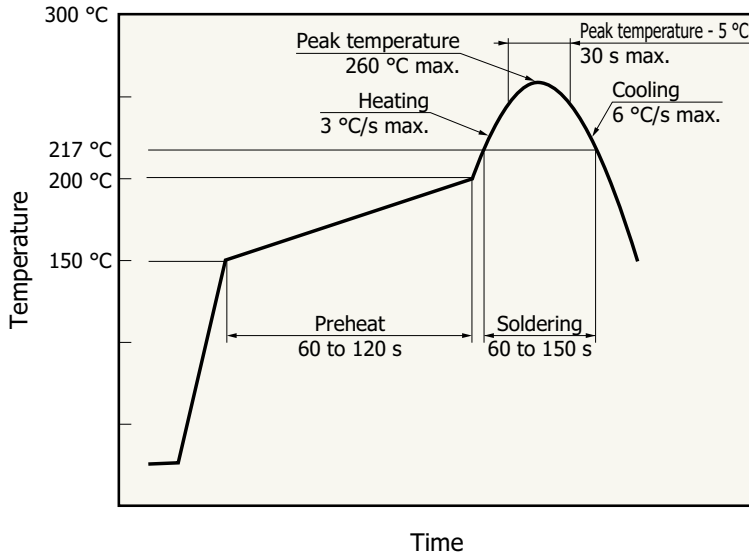
- Embossed tape (unit: mm, material: PS, conductive)



KAPDC0139EA

- Packing quantity
1000 pcs/reel
- Packing state
Reel and desiccant in moisture-proof packaging (vacuum-sealed)

Recommended reflow soldering conditions



KMPDB0405EC

- After unpacking, store it in an environment at a temperature of 30 °C or less and a humidity of 60% or less, and perform soldering within 4 weeks.
- The effect that the product receives during reflow soldering varies depending on the circuit board and reflow oven that are used. When you set reflow soldering conditions, check that problems do not occur in the product by testing out the conditions in advance.

Baking

If three months have passed without unpacking or the above storage period has passed after unpacking, perform baking before reflow soldering to dehumidify. For the baking, refer to the precautions "Surface mount type products."

Recommended baking conditions

- Temperature: 150 °C, 3 hours, up to twice

Note: When you set baking conditions, check that problems do not occur in the product by testing out the conditions in advance.

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

Precautions

- Disclaimer
- Surface mount type products

Technical note

- Si APD

The content of this document is current as of February 2024.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

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